



WIDE BANDWIDTH DUAL J-FET OPERATIONAL AMPLIFIERS

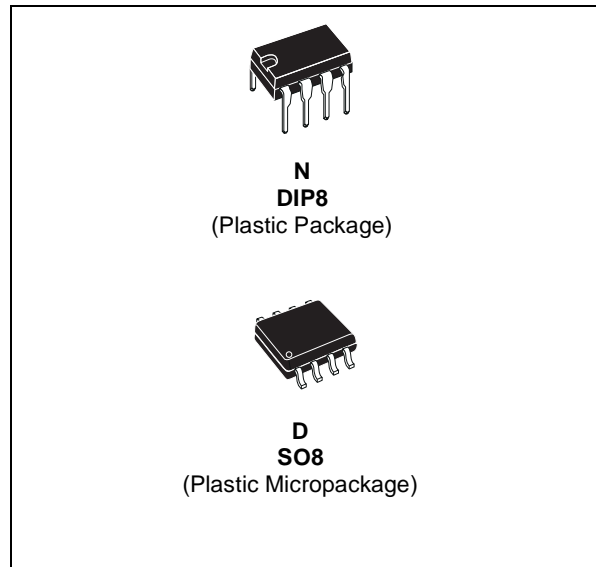
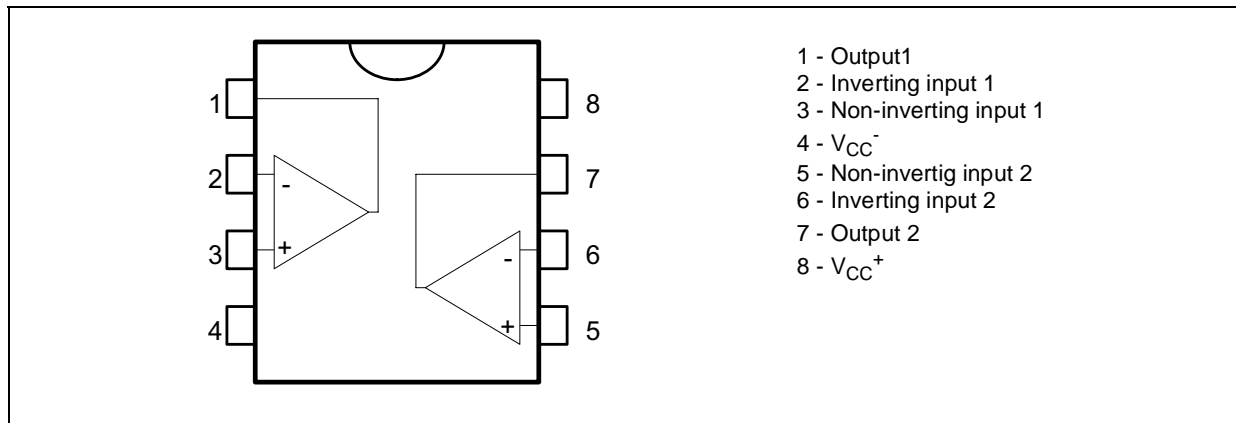
- LOW POWER CONSUMPTION
- WIDE COMMON-MODE (UP TO V_{CC}^+) AND DIFFERENTIAL VOLTAGE RANGE
- LOW INPUT BIAS AND OFFSET CURRENT
- OUTPUT SHORT-CIRCUIT PROTECTION
- HIGH INPUT IMPEDANCE J-FET INPUT STAGE
- INTERNAL FREQUENCY COMPENSATION
- LATCH UP FREE OPERATION
- HIGH SLEW RATE : $16V/\mu s$ (typ)

DESCRIPTION

The LF353 are high speed J-FET input dual operational amplifiers incorporating well matched, high voltage J-FET and bipolar transistors in a monolithic integrated circuit.

The devices feature high slew rates, low input bias and offset currents, and low offset voltage temperature coefficient.

PIN CONNECTIONS (top view)

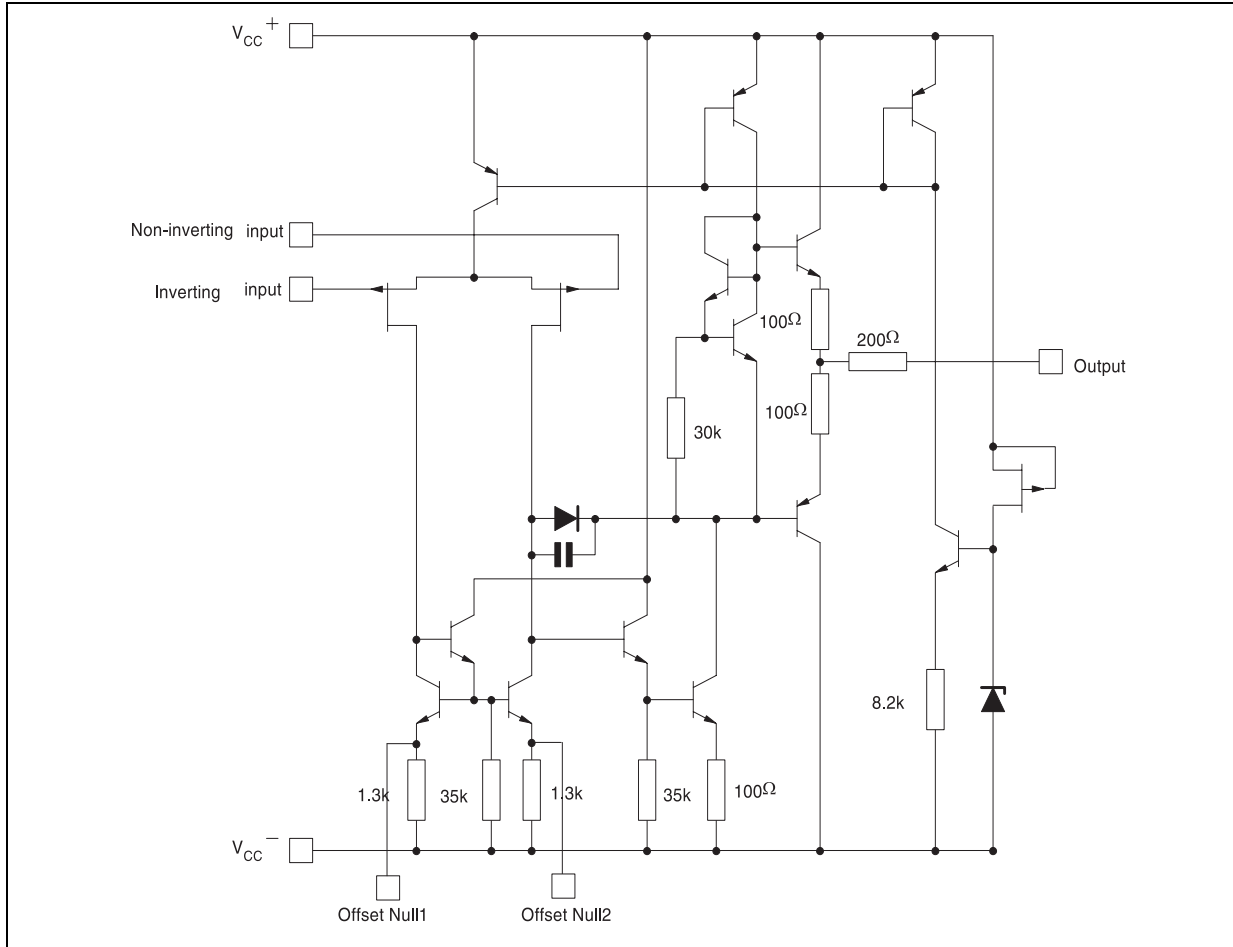


ORDER CODE

Part Number	Temperature Range	Package	
		N	D
LF353	0°C, +70°C	•	•
LF253	-40°C, +105°C	•	•
LF153	-55°C, +125°C	•	•

N = Dual in Line Package (DIP)
D = Small Outline Package (SO) - also available in Tape & Reel (DT)

SCHEMATIC DIAGRAM (each amplifier)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	LF153	LF253	LF353	Unit
V_{CC}	Supply voltage - note ¹⁾		±18		V
V_i	Input Voltage - note ²⁾		±15		V
V_{id}	Differential Input Voltage - note ³⁾		±30		V
P_{tot}	Power Dissipation		680		mW
	Output Short-circuit Duration - note ⁴⁾		Infinite		
T_{oper}	Operating Free-air Temperature Range	-55 to +125	-40 to +105	0 to +70	°C
T_{stg}	Storage Temperature Range	-65 to +150			°C

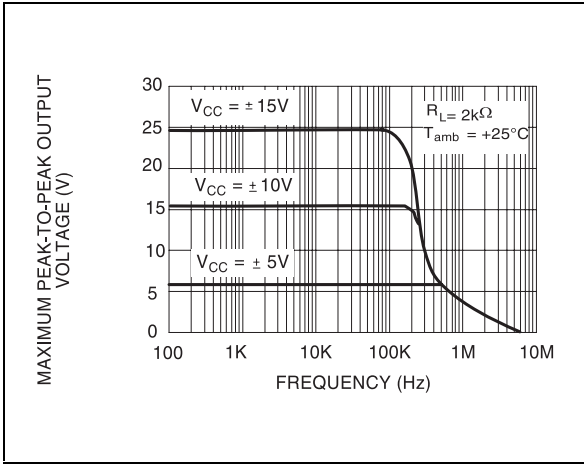
1. All voltage values, except differential voltage, are with respect to the zero reference level (ground) of the supply voltages where the zero reference level is the midpoint between V_{CC+} and V_{CC-} .
2. The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 volts, whichever is less.
3. Differential voltages are the non-inverting input terminal with respect to the inverting input terminal.
4. The output may be shorted to ground or to either supply. Temperature and/or supply voltages must be limited to ensure that the dissipation rating is not exceeded.

ELECTRICAL CHARACTERISTICS
 $V_{CC} = \pm 15V, T_{amb} = +25^{\circ}C$ (unless otherwise specified)

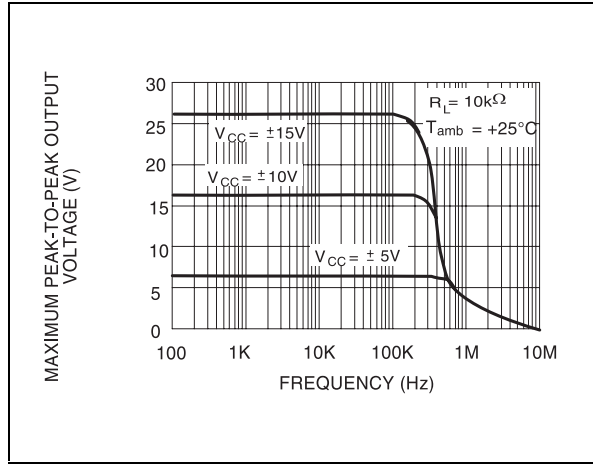
Symbol	Parameter	Min.	Typ.	Max.	Unit
V_{io}	Input Offset Voltage ($R_S = 10k\Omega$) $T_{amb} = +25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$		3	10 13	mV
DV_{io}	Input Offset Voltage Drift		10		$\mu V/^{\circ}C$
I_{io}	Input Offset Current- note 1) $T_{amb} = +25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$		5	100 4	pA nA
I_{ib}	Input Bias Current -note 1 $T_{amb} = +25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$		20	200 20	nA
A_{vd}	Large Signal Voltage Gain ($R_L = 2k\Omega, V_o = \pm 10V$) $T_{amb} = +25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$	50 25	200		V/mV
SVR	Supply Voltage Rejection Ratio ($R_S = 10k\Omega$) $T_{amb} = +25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$	80 80	86		dB
I_{CC}	Supply Current, no load $T_{amb} = +25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$		1.4	3.2 3.2	mA
V_{icm}	Input Common Mode Voltage Range	± 11	+15 -12		V
CMR	Common Mode Rejection Ratio ($R_S = 10k\Omega$) $T_{amb} = +25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$	70 70	86		dB
I_{OS}	Output Short-circuit Current $T_{amb} = +25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$	10 10	40	60 60	mA
$\pm V_{opp}$	Output Voltage Swing $T_{amb} = +25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$				V
	$R_L = 2k\Omega$	10	12		
	$R_L = 10k\Omega$	12	13.5		
	$R_L = 2k\Omega$	10			
	$R_L = 10k\Omega$	12			
SR	Slew Rate $V_i = 10V, R_L = 2k\Omega, C_L = 100pF, T_{amb} = +25^{\circ}C, \text{unity gain}$	12	16		V/ μs
t_r	Rise Time $V_i = 20mV, R_L = 2k\Omega, C_L = 100pF, T_{amb} = +25^{\circ}C, \text{unity gain}$		0.1		μs
K_{ov}	Overshoot $V_i = 20mV, R_L = 2k\Omega, C_L = 100pF, T_{amb} = +25^{\circ}C, \text{unity gain}$		10		%
GBP	Gain Bandwidth Product $f = 100kHz, T_{amb} = +25^{\circ}C, V_{in} = 10mV, R_L = 2k\Omega, C_L = 100pF$	2.5	4		MHz
R_i	Input Resistance		10^{12}		Ω
THD	Total Harmonic Distortion ($f = 1kHz, A_v = 20dB$ $R_L = 2k\Omega, C_L = 100pF, T_{amb} = +25^{\circ}C, V_o = 2V_{pp}$)		0.01		
e_n	Equivalent Input Noise Voltage $R_S = 100\Omega, f = 1KHz$		15		$\frac{nV}{\sqrt{Hz}}$
ϕ_m	Phase Margin		45		Degrees
V_{o1}/V_{o2}	Channel Separation ($A_v = 100, T_{amb} = +25^{\circ}C$)		120		dB

1. The input bias currents are junction leakage currents which approximately double for every 10°C increase in the junction temperature.

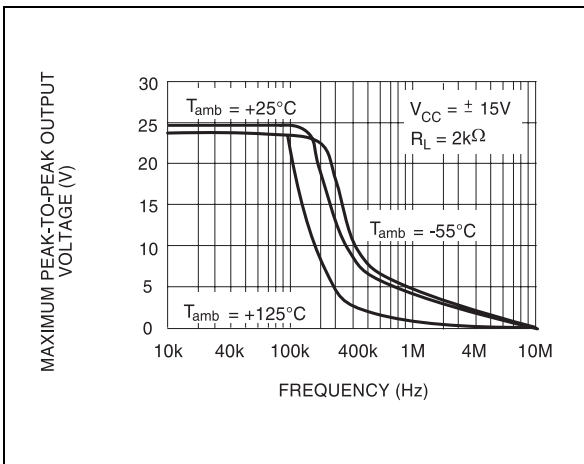
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE versus FREQUENCY



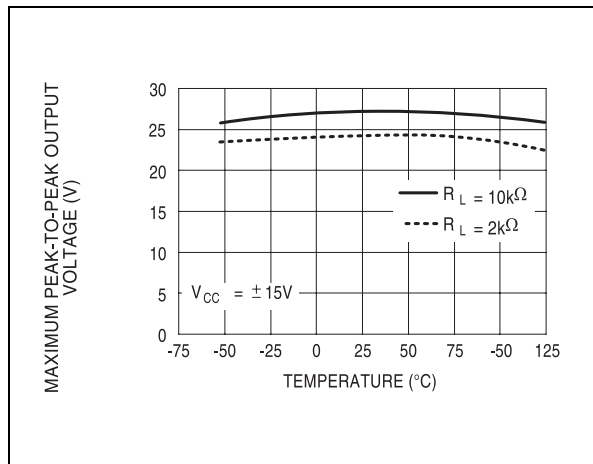
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE versus FREQUENCY



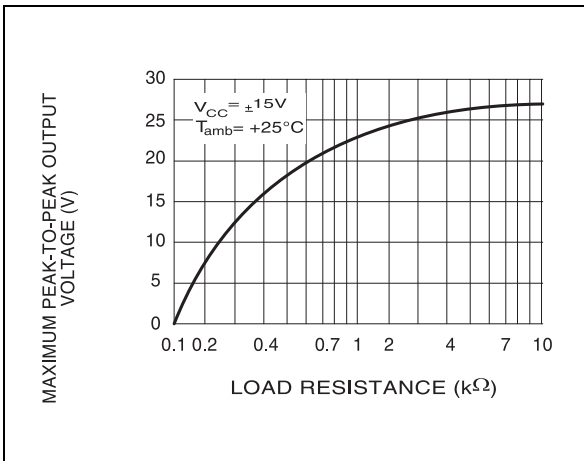
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE versus FREQUENCY



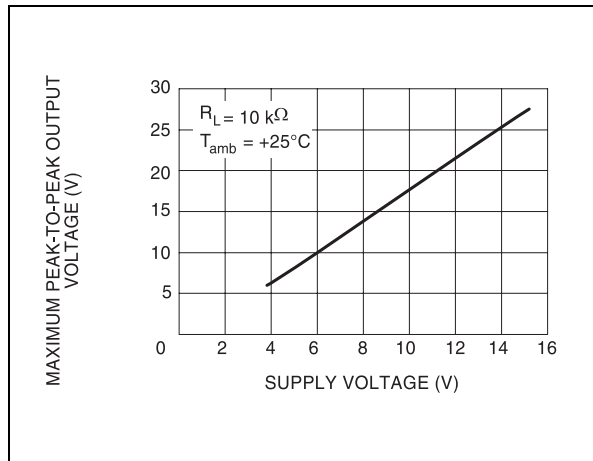
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE versus FREE AIR TEMP.



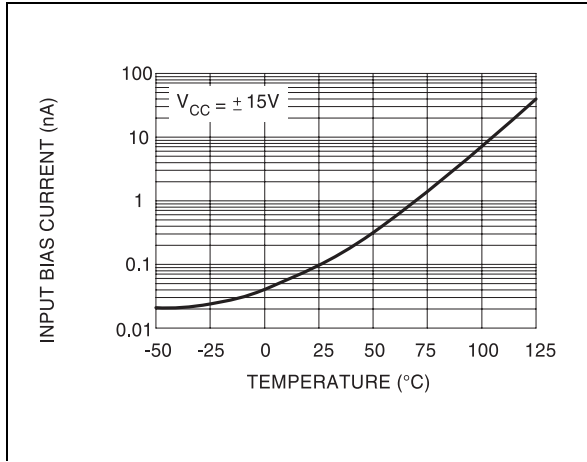
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE versus LOAD RESISTANCE



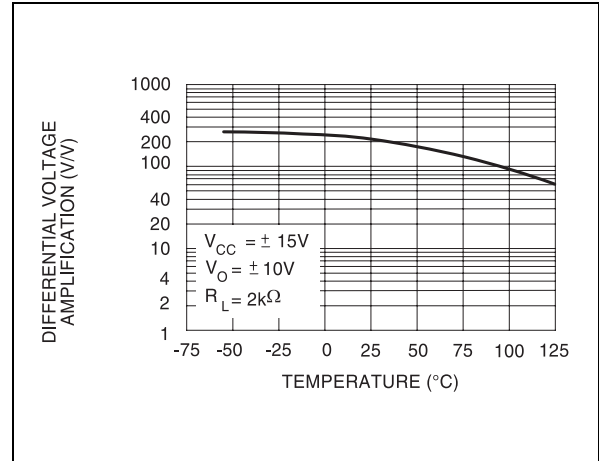
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE versus SUPPLY VOLTAGE



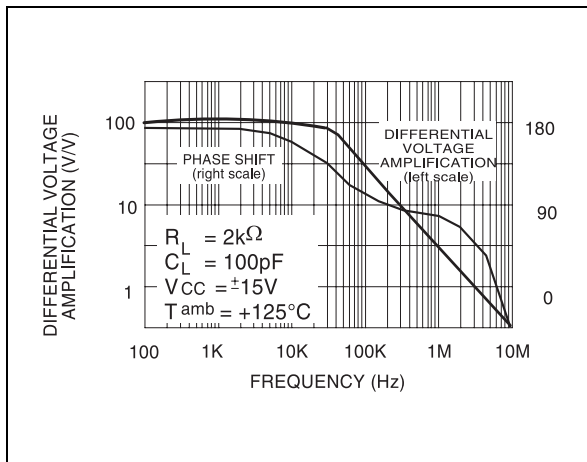
INPUT BIAS CURRENT versus FREE AIR TEMPERATURE



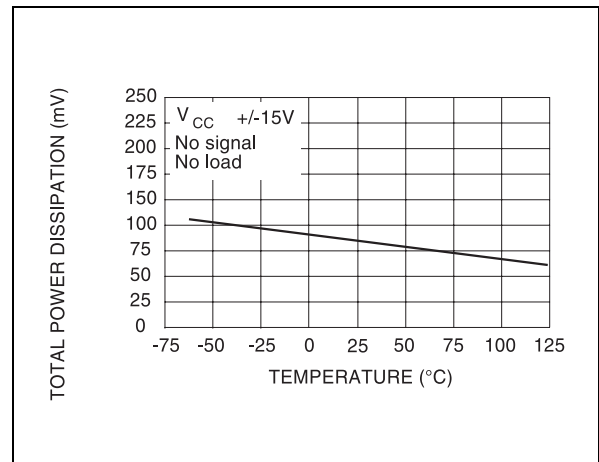
LARGE SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION versus FREE AIR TEMP.



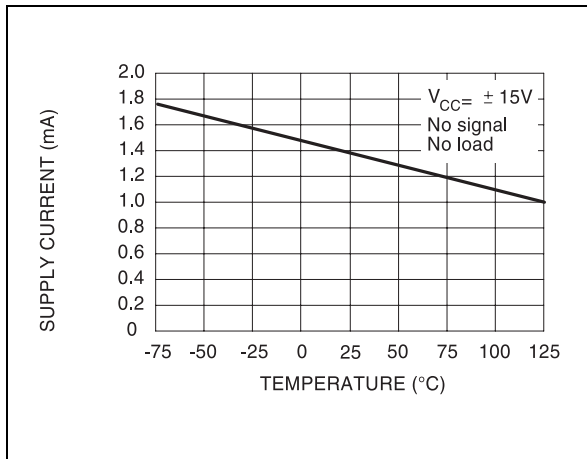
LARGE SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT versus FREQUENCY



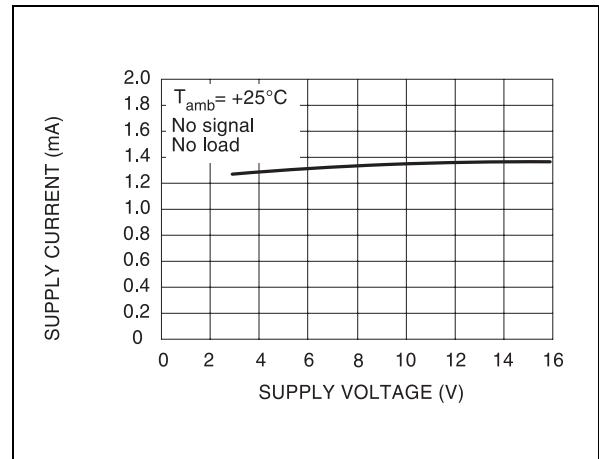
TOTAL POWER DISSIPATION versus FREE AIR TEMPERATURE



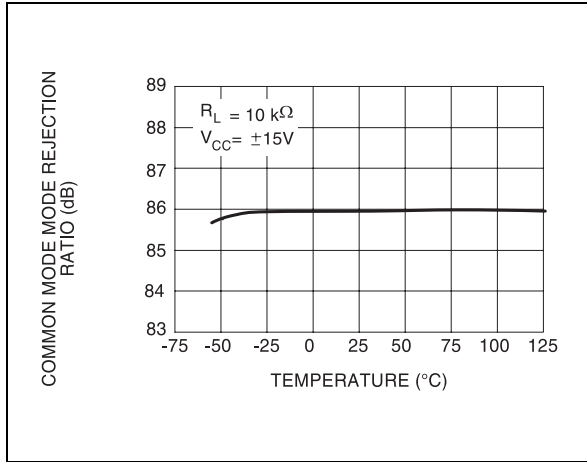
SUPPLY CURRENT PER AMPLIFIER versus FREE AIR TEMPERATURE



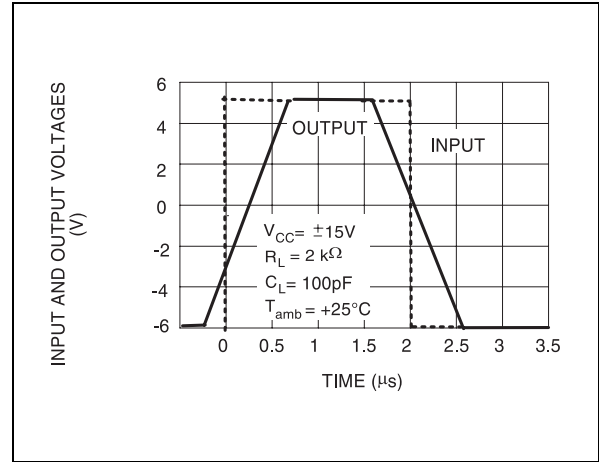
SUPPLY CURRENT PER AMPLIFIER versus SUPPLY VOLTAGE



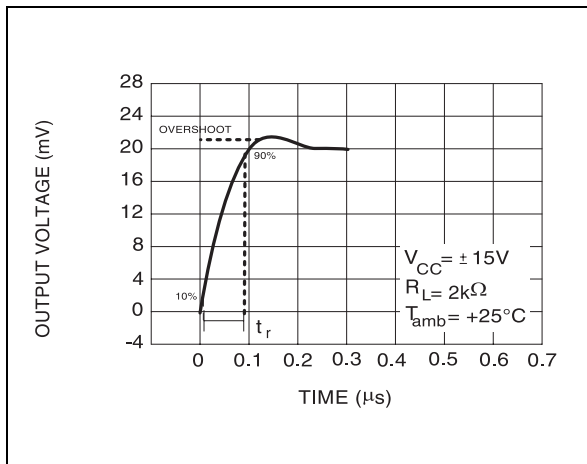
COMMON MODE REJECTION RATIO versus FREE AIR TEMPERATURE



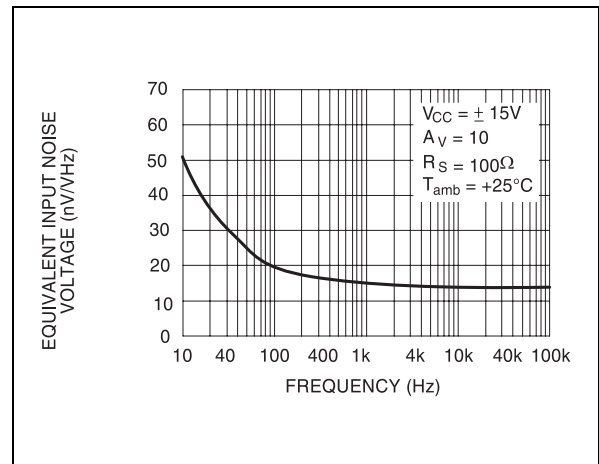
VOLTAGE FOLLOWER LARGE SIGNAL PULSE RESPONSE



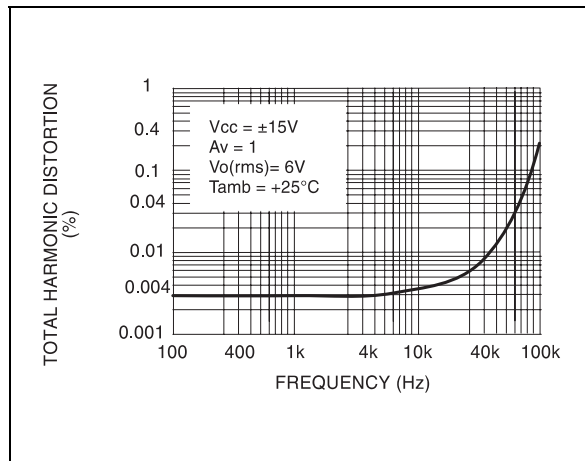
OUTPUT VOLTAGE versus ELAPSED TIME



EQUIVALENT INPUT NOISE VOLTAGE versus FREQUENCY



TOTAL HARMONIC DISTORTION versus FREQUENCY



PARAMETER MEASUREMENT INFORMATION

Figure 1 : Voltage Follower

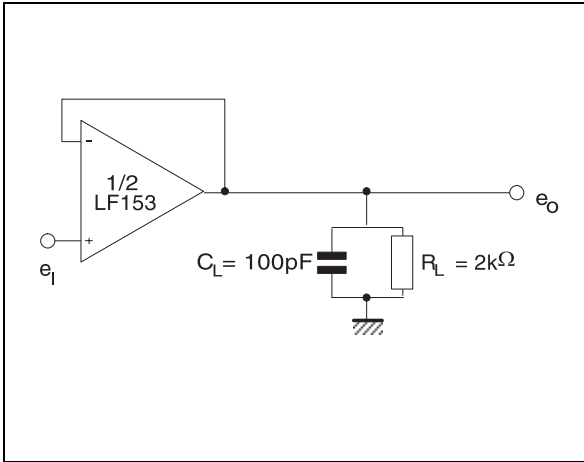
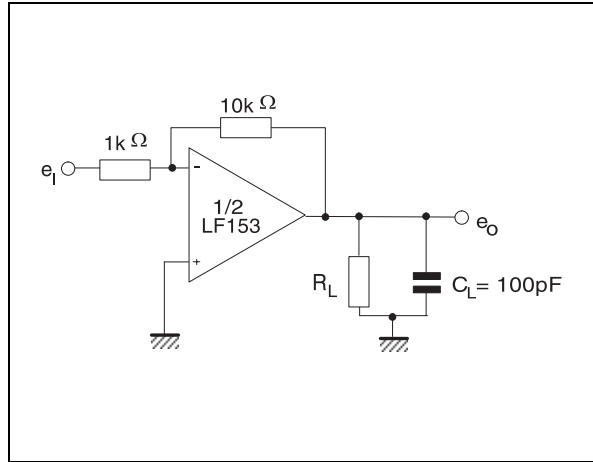
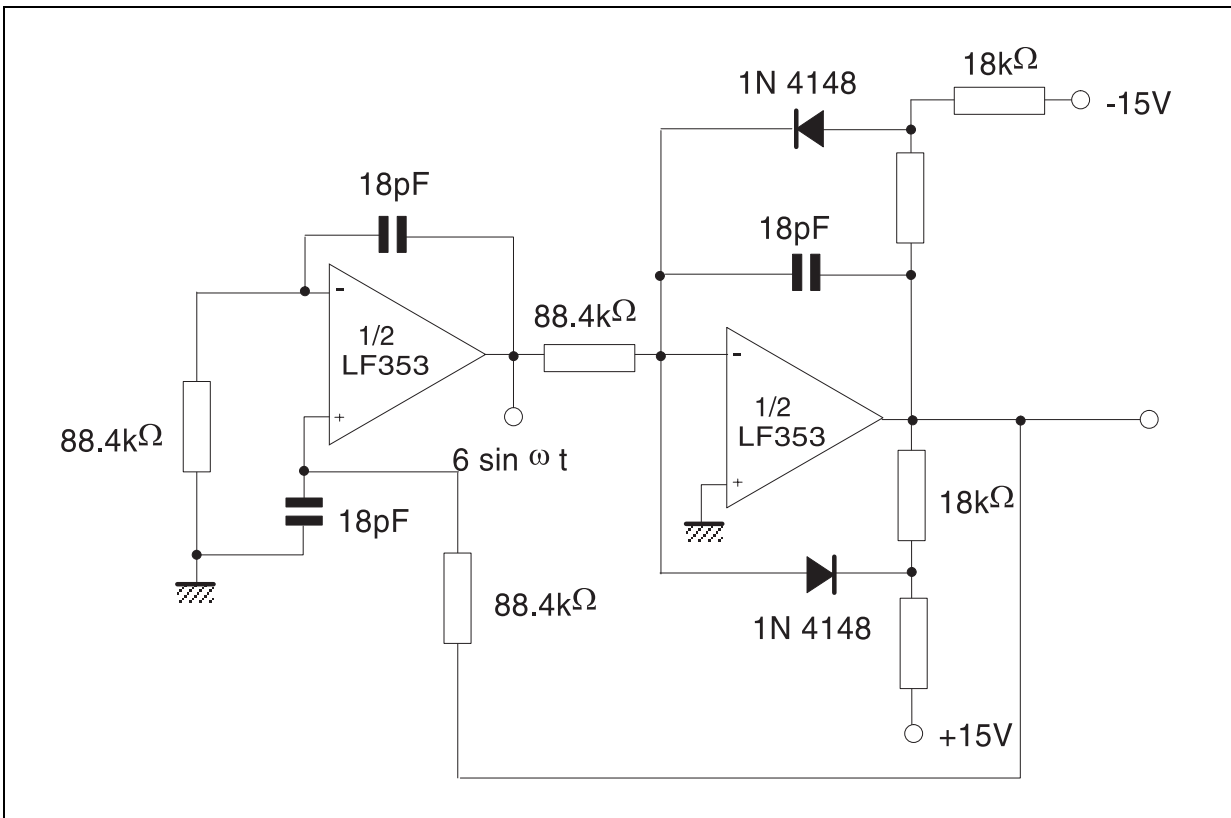


Figure 2 : Gain-of-10 inverting amplifier

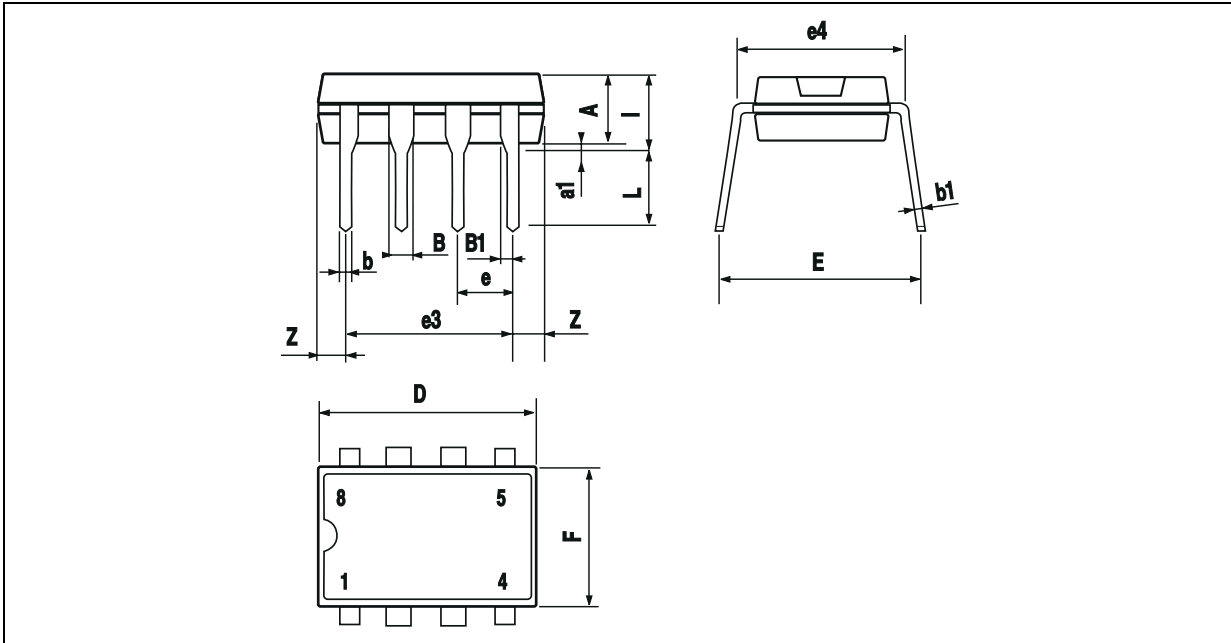


TYPICAL APPLICATION

QUADRUPLE OSCILLATOR

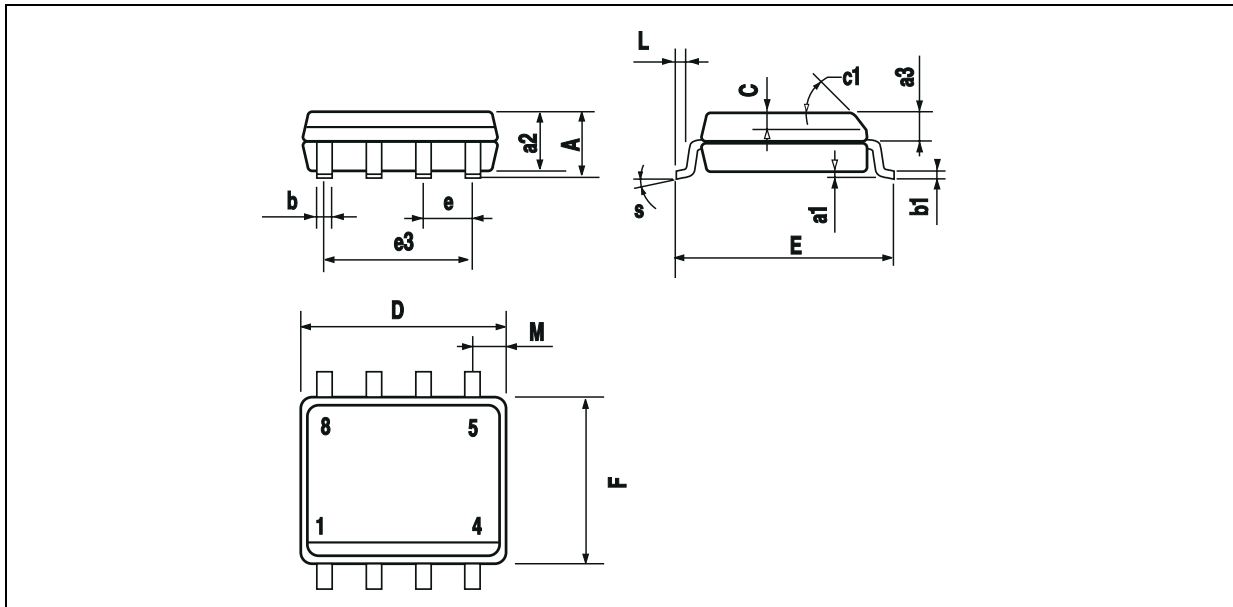


PACKAGE MECHANICAL DATA
8 PINS - PLASTIC DIP



Dim.	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A		3.32			0.131	
a1	0.51			0.020		
B	1.15		1.65	0.045		0.065
b	0.356		0.55	0.014		0.022
b1	0.204		0.304	0.008		0.012
D			10.92			0.430
E	7.95		9.75	0.313		0.384
e		2.54			0.100	
e3		7.62			0.300	
e4		7.62			0.300	
F			6.6			0.260
i			5.08			0.200
L	3.18		3.81	0.125		0.150
Z			1.52			0.060

PACKAGE MECHANICAL DATA
8 PINS - PLASTIC MICROPACKAGE (SO)



Dim.	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.75			0.069
a1	0.1		0.25	0.004		0.010
a2			1.65			0.065
a3	0.65		0.85	0.026		0.033
b	0.35		0.48	0.014		0.019
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.020
c1	45° (typ.)					
D	4.8		5.0	0.189		0.197
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.150		0.157
L	0.4		1.27	0.016		0.050
M			0.6			0.024
S	8° (max.)					

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